SN74CBTD3384C 10-BIT FET BUS SWITCH WITH LEVEL SHIFTING 5-V BUS SWITCH WITH –2-V UNDERSHOOT PROTECTION

SCDS133A -SEPTEMBER 2003 - REVISED OCTOBER 2003

- Undershoot Protection for Off-Isolation on A and B Ports Up To -2 V
- Integrated Diode to V_{CC} Provides 5-V Input Down To 3.3-V Output Level Shift
- Bidirectional Data Flow, With Near-Zero Propagation Delay
- Low ON-State Resistance (ron) Characteristics (ron = 3 Ω Typical)
- Low Input/Output Capacitance Minimizes Loading and Signal Distortion (C_{io(OFF)} = 5 pF Typical)
- Data and Control Inputs Provide Undershoot Clamp Diodes
- V_{CC} Operating Range From 4.5 V to 5.5 V

- Data I/Os Support 0 to 5-V Signaling Levels (0.8-V, 1.2-V, 1.5-V, 1.8-V, 2.5-V, 3.3-V, 5-V)
- Control Inputs Can be Driven by TTL or 5-V/3.3-V CMOS Outputs
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22

 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)
- Supports Both Digital and Analog Applications: Memory Interleaving, Bus Isolation, Low-Distortion Signal Gating

DB, DBQ, DGV, DW, OR PW PACKAGE (TOP VIEW)									
1 OE [1B1 [1A1 [1A2 [1B3 [1A3 [1A4 [1B5 [1A5 [GND [1 2 3 4 5 6 7 8 9 10 11 12	24 23 22 21 20 19 18 17 16 15 14 13	V _{CC} 2B5 2A5 2A4 2B4 2B3 2A3 2A2 2B2 2B1 2A1 2OE						

description/ordering information

ORDERING INFORMATION

TA	PACKAGI	PACKAGE [†]		TOP-SIDE MARKING	
	SOIC - DW	Tube	SN74CBTD3384CDW		
	SOIC - DW	Tape and reel	SN74CBTD3384CDWR	CBTD3384C	
		Tube	SN74CBTD3384CDB	000040	
–40°C to 85°C	SSOP – DB	Tape and reel	SN74CBTD3384CDBR	CC384C	
-40 C 10 85 C	SSOP (QSOP) – DBQ	Tape and reel	SN74CBTD3384CDBQR	CBTD3384C	
	TOOOD DW/	Tube	SN74CBTD3384CPW		
	TSSOP – PW	Tape and reel	SN74CBTD3384CPWR	CC384C	
	TVSOP – DGV	Tape and reel	SN74CBTD3384CDGVR	CC384C	

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



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SN74CBTD3384C 10-BIT FET BUS SWITCH WITH LEVEL SHIFTING 5-V BUS SWITCH WITH –2-V UNDERSHOOT PROTECTION

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description/ordering information (continued)

The SN74CBTD3384C is a high-speed TTL-compatible FET bus switch with low ON-state resistance (ron), allowing for minimal propagation delay. This device features an integrated diode in series with V_{CC} to provide level shifting for 5-V input down to 3.3-V output levels. Active Undershoot-Protection Circuitry on the A and B ports of the SN74CBTD3384C provides protection for undershoot up to -2 V by sensing an undershoot event and ensuring that the switch remains in the proper OFF state.

The SN74CBTD3384C is organized as two 5-bit bus switches with separate output-enable (1OE, 2OE) inputs. It can be used as two 5-bit bus switches or as one 10-bit bus switch. When \overline{OE} is low, the associated 5-bit bus switch is ON, and the A port is connected to the B port, allowing bidirectional data flow between ports. When OE is high, the associated 5-bit bus switch is OFF, and a high-impedance state exists between the A and B ports.

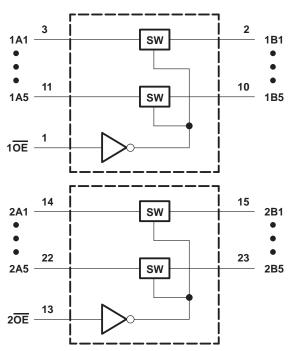
This device is fully specified for partial-power-down applications using Ioff. The Ioff feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off.

To ensure the high-impedance state during power up or power down, OE should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

	INPUT/OUTPUT A	FUNCTION
L	В	A port = B port
Н	Z	Disconnect

FUNCTION TABLE (each 5-bit bus switch)

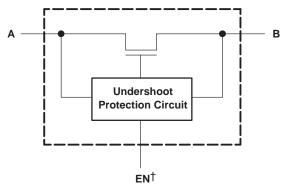
logic diagram (positive logic)





SN74CBTD3384C 10-BIT FET BUS SWITCH WITH LEVEL SHIFTING 5-V BUS SWITCH WITH –2-V UNDERSHOOT PROTECTION SCDS133A – SEPTEMBER 2003 – REVISED OCTOBER 2003

simplified schematic, each FET switch (SW)



[†] EN is the internal enable signal applied to the switch.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[‡]

Supply voltage range, V _{CC} Control input voltage range, V _{IN} (see Notes 1 a		
Switch I/O voltage range, VI/O (see Notes 1, 2,		
Control input clamp current, I _{IK} (V _{IN} < 0)		
I/O port clamp current, $I_{I/OK}$ ($V_{I/O} < 0$)		
ON-state switch current, II/O (see Note 4)		±128 mA
Continuous current through V _{CC} or GND termin	nals	±100 mA
Package thermal impedance, θ_{JA} (see Note 5):	DB package	63°C/W
-	DBQ package	61°C/W
	DGV package	
	DW package	46°C/W
	PW package	
Storage temperature range, T _{stg}		–65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltages are with respect to ground unless otherwise specified.
 - 2. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 - 3. VI and VO are used to denote specific conditions for $V_{I/O}$.
 - 4. II and IO are used to denote specific conditions for $I_{I/O}$.
 - 5. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Notes 6 and 7)

		MIN	MAX	UNIT
VCC	Supply voltage	4.5	5.5	V
VIH	High-level control input voltage	2	5.5	V
V_{IL}	Low-level control input voltage	0	0.8	V
V _{I/O}	Data input/output voltage	0	5.5	V
TA	Operating free-air temperature	-40	85	°C

NOTES: 6. All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

7. In applications with fast edge rates, multiple outputs switching, and operating at high frequencies, the output may have little or no level-shifting effect.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PA	RAMETER		TEST CONDITIO	NS	MIN TYPT	MAX	UNIT
VIK	Control inputs	V _{CC} = 4.5 V,	I _{IN} = -18 mA			-1.8	V
VIKU	Data inputs	V _{CC} = 5 V,	0 mA > I _I \ge -50 mA, V _{IN} = V _{CC} or GND, Switch OFF			-2	V
VOH		See Figures 4 and 5					
I _{IN}	Control inputs	V _{CC} = 5.5 V,	$V_{IN} = V_{CC} \text{ or } GND$			±1	μΑ
I _{OZ} ‡		V _{CC} = 5.5 V,	$V_{O} = 0$ to 5.5 V, $V_{I} = 0$,	Switch OFF, V _{IN} = V _{CC} or GND		±10	μΑ
loff		$V_{CC} = 0,$	V _O = 0 to 5.5 V,	V I = 0		10	μA
ICC		V _{CC} = 5.5 V,	$I_{I/O} = 0,$ $V_{IN} = V_{CC} \text{ or GND},$	Switch ON or OFF		1.5	mA
∆ICC§	Control inputs	V _{CC} = 5.5 V,	One input at 3.4 V,	Other inputs at V_{CC} or GND		2.5	mA
C _{in}	Control inputs	$V_{IN} = 3 V \text{ or } 0$			3.5		pF
C _{io(OFF}	-)	$V_{I/O} = 3 V \text{ or } 0,$	Switch OFF,	$V_{IN} = V_{CC}$ or GND	5		pF
C _{io(ON)}		VI/O = 3 V or 0,	Switch ON,	V _{IN} = V _{CC} or GND	12.5		pF
				IO = 64 mA	3	6	
ron¶		$V_{CC} = 4.5 V$	$V_{I} = 0$	I _O = 30 mA	3	6	Ω
			V _I = 2.4 V,	I _O = -15 mA	8	20	

VIN and IIN refer to control inputs. VI, VO, II, and IO refer to data pins.

[†] All typical values are at V_{CC} = 5 V (unless otherwise noted), T_A = 25°C.

[‡] For I/O ports, the parameter I_{OZ} includes the input leakage current.

§ This is the increase in supply current for each input that is at the specified voltage level, rather than V_{CC} or GND.

¶ Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

PARAMETER	FROM	TO	= V _{CC} ± 0.	≡ 5 V 5 V	UNIT
	(INPUT)	(OUTPUT)	MIN	MAX	
tpd [#]	A or B	B or A		0.15	ns
ten	ŌĒ	A or B	1.5	4.8	ns
^t dis	OE	A or B	1.5	4.8	ns

[#]The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).



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undershoot characteristics (see Figures 1 and 2)

	PARAMETER	TEST CONDITIONS MIN TYP [†] MAX							
	Voutu	$V_{CC} = 5.5 \text{ V}$, Switch OFF, $V_{IN} = V_{CC} \text{ or GND}$	2	V _{OH} -0.3		V			
1	Fault in the state of the state								

[†] All typical values are at $V_{CC} = 5 V$ (unless otherwise noted), $T_A = 25^{\circ}C$.

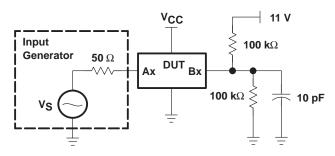


Figure 1. Device Test Setup

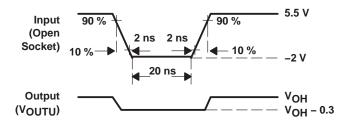
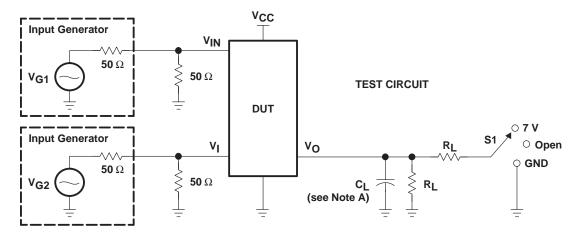


Figure 2. Transient Input Voltage (V_I) and Output Voltage (V_{OUTU}) Waveforms (Switch OFF)

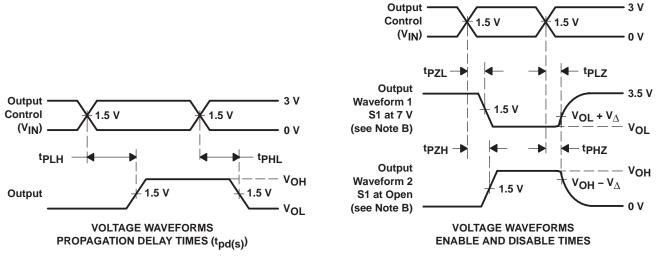


SN74CBTD3384C **10-BIT FET BUS SWITCH WITH LEVEL SHIFTING** 5-V BUS SWITCH WITH –2-V UNDERSHOOT PROTECTION SCDS133A -SEPTEMBER 2003 - REVISED OCTOBER 2003

PARAMETER MEASUREMENT INFORMATION FOR LEVEL SHIFTER



TEST	VCC	S1	RL	٧I	CL	v_Δ
^t pd(s)	5 V \pm 0.5 V	Open	500 Ω	V _{CC} or GND	50 pF	
tPLZ/tPZL	5 V \pm 0.5 V	7 V	500 Ω	GND	50 pF	0.3 V
^t PHZ ^{/t} PZH	5 V \pm 0.5 V	Open	500 Ω	v _{cc}	50 pF	0.3 V



NOTES: A. CL includes probe and jig capacitance.

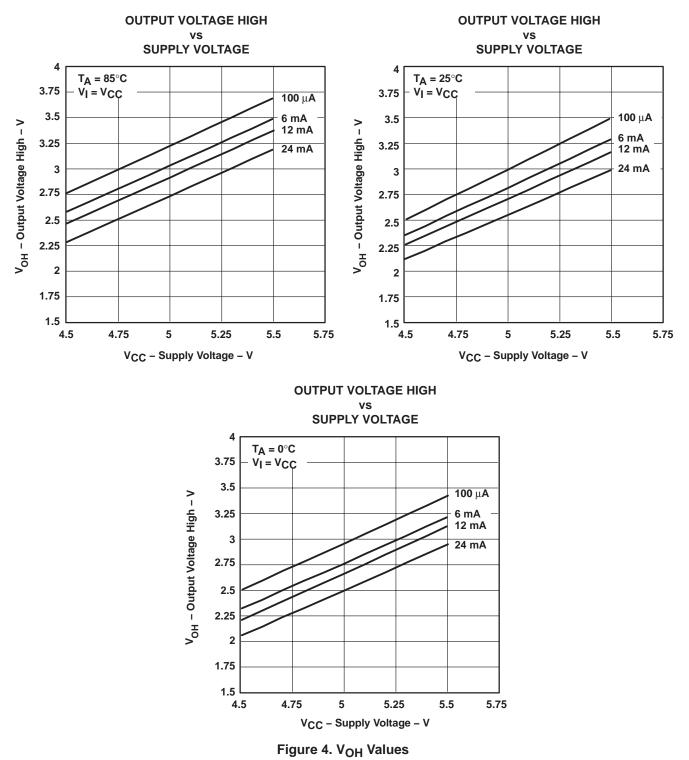
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_Q = 50 Ω , t_r \leq 2.5 ns, t_f \leq 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd(s). The tpd propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
- H. All parameters and waveforms are not applicable to all devices.





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TYPICAL CHARACTERISTICS

SN74CBTD3384C 10-BIT FET BUS SWITCH WITH LEVEL SHIFTING 5-V BUS SWITCH WITH -2-V UNDERSHOOT PROTECTION SCDS133A -SEPTEMBER 2003 - REVISED OCTOBER 2003

TYPICAL CHARACTERISTICS (continued)

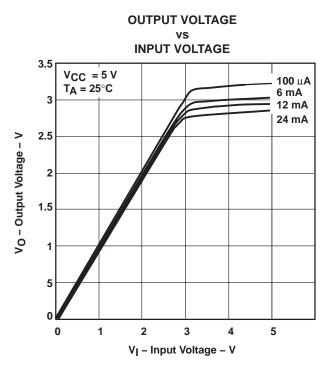


Figure 5. Data Output Voltage vs Data Input Voltage





PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
74CBTD3384CDGVRE4	ACTIVE	TVSOP	DGV	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C	Samples
74CBTD3384CDGVRG4	ACTIVE	TVSOP	DGV	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C	Samples
SN74CBTD3384CDBQR	ACTIVE	SSOP	DBQ	24	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CBTD3384C	Samples
SN74CBTD3384CDBR	ACTIVE	SSOP	DB	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C	Samples
SN74CBTD3384CDGVR	ACTIVE	TVSOP	DGV	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C	Samples
SN74CBTD3384CDW	ACTIVE	SOIC	DW	24	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTD3384C	Samples
SN74CBTD3384CDWR	ACTIVE	SOIC	DW	24	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	CBTD3384C	Samples
SN74CBTD3384CDWRG4	ACTIVE	SOIC	DW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTD3384C	Samples
SN74CBTD3384CPW	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C	Samples
SN74CBTD3384CPWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C	Samples
SN74CBTD3384CPWRE4	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CC384C	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



PACKAGE OPTION ADDENDUM

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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STRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



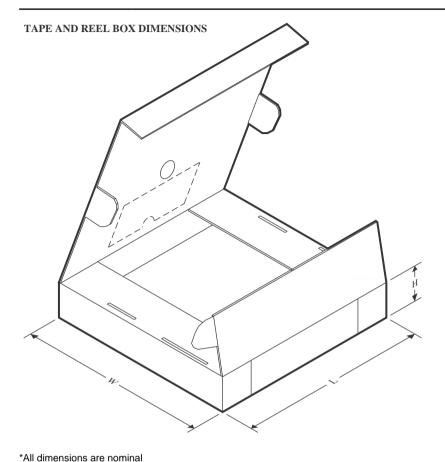
*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CBTD3384CDBQR	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74CBTD3384CDBR	SSOP	DB	24	2000	330.0	16.4	8.2	8.8	2.5	12.0	16.0	Q1
SN74CBTD3384CDGVR	TVSOP	DGV	24	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CBTD3384CDWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
SN74CBTD3384CDWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
SN74CBTD3384CDWRG4	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
SN74CBTD3384CPWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1



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PACKAGE MATERIALS INFORMATION

3-Jun-2022



Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74CBTD3384CDBQR	SSOP	DBQ	24	2500	356.0	356.0	35.0
SN74CBTD3384CDBR	SSOP	DB	24	2000	356.0	356.0	35.0
SN74CBTD3384CDGVR	TVSOP	DGV	24	2000	367.0	367.0	35.0
SN74CBTD3384CDWR	SOIC	DW	24	2000	364.0	361.0	36.0
SN74CBTD3384CDWR	SOIC	DW	24	2000	350.0	350.0	43.0
SN74CBTD3384CDWRG4	SOIC	DW	24	2000	350.0	350.0	43.0
SN74CBTD3384CPWR	TSSOP	PW	24	2000	356.0	356.0	35.0

TEXAS INSTRUMENTS

www.ti.com

3-Jun-2022

TUBE



- B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
SN74CBTD3384CDW	DW	SOIC	24	25	506.98	12.7	4826	6.6
SN74CBTD3384CPW	PW	TSSOP	24	60	530	10.2	3600	3.5

DBQ (R-PDSO-G24)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.

D. Falls within JEDEC MO-137 variation AE.



PW0024A



PACKAGE OUTLINE

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



PW0024A

EXAMPLE BOARD LAYOUT

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PW0024A

EXAMPLE STENCIL DESIGN

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



MECHANICAL DATA

PLASTIC SMALL-OUTLINE

MPDS006C - FEBRUARY 1996 - REVISED AUGUST 2000

DGV (R-PDSO-G**)

24 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
- D. Falls within JEDEC: 24/48 Pins MO-153

14/16/20/56 Pins – MO-194



DW (R-PDSO-G24)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

D. Falls within JEDEC MS-013 variation AD.



LAND PATTERN DATA



NOTES:

A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



MECHANICAL DATA

MSSO002E - JANUARY 1995 - REVISED DECEMBER 2001

DB (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

28 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
- D. Falls within JEDEC MO-150



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